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Docket No.: M4065.0479/P479
(PATENT)

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper et al.

Art Unit: 2818

Application No.: 10/076,486

Examiner: M. Tran

Filed: February 19, 2002

Allowed: April 26, 2004

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

REQUEST FOR ACKNOWLEDGEMENT OF FORMS PTO-1449

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

After review of the above-captioned application file after allowance, it has come to the undersigned attorneys' attention that Forms PTO-1449, which accompanied a Second Information Disclosure Statement filed September 26, 2002 and a Third Information Disclosure Statement filed September 16, 2003 have yet to be acknowledged by the Examiner. Copies of the two Information Disclosure Statements are attached

hereto, together with copies of the date-stamped postcards evidencing the filing of same. The Examiner is respectfully requested to return the initialed forms to the undersigned attorneys as soon as possible.

Dated: June 3, 2004

Respectfully submitted,

By 

Thomas J. D'Amico

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Attorneys for Applicants



Atty Docket No.. 14065.0479/P479 ✓

Inventors: Stephen L. Casper et al.

pplication No.: 10/076,486

Filing Date: February 19, 2002

itle: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR
SENSING SAME

ocuments Filed:

Second Information Disclosure Statement w/Form PTO/SB/08A and 170 references



ia: PTO Daily Run

Date: September 26, 2002

ender's Initials: TJD/SPT/rrl

RAW 9/26/02

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Docket No.: M4065.0479/P479
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Stephen L. Casper et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: Not Known

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

SECOND INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

A brief explanation of relevance of the non-patent documents listed on form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is "material" or that it qualifies as prior art. The Examiner is respectfully requested to utilize Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.

Documents discussed in Appendix A marked with an asterisk (*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Second Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that the Second Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Commissioner is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0479/P479.

Dated: September 26, 2002

Respectfully submitted,

By

Thomas J. D'Amico

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Attorneys for Applicant(s)

APPENDIX A

Abdel-All, et al., Vacuum 59 (2000) 845-853: published in December, this document generally relates to, inter alia, the electrical properties of $Ge_5As_{38}Te_{57}$ as a function of temperature.

*Adler and Moss, J. Vac. Sci. Technol. 9 (1972) 1182-1189: this document generally relates to, inter alia, two types of electrical/material switching – threshold and memory, in amorphous materials; the effects of temperature, pressure, and frequency on switching; and the physics of threshold voltage and memory.

Adler et al., Ref. Mod. Phys. 50 (1978) 209-220: this document generally relates to, inter alia, threshold switching in amorphous alloys, state (“on” and “off”) characteristics, and glass properties.

Afifi, et al., Appl. Phys. A 55 (1992) 167-169: this document generally relates to, inter alia, SeGe-Sb glasses.

*Afifi, et al., J. Phys. 17 (1986) 335-342: this document generally relates to, inter alia, electrical and thermal conductivity of Ge_xSe_{1-x} compositions as a function of temperature. $Ge_{25}Se_{75}$ stoichiometry is disclosed.

Alekperova and Gadzhieva, 23 (1987) 137-139: this document generally relates to, inter alia, a characteristic diode state in Ag_2Se compositions upon heating (to 376-400°K).

*Aleksiejunas and Cesnys, Phys. Stat. Sol. (a) 19 (1973) K169-K171: this document generally relates to, inter alia, the subjects of selenium investigation and how $Se-Ag_2Se$ contributes silver ions to a selenium composition.

Angell, Annu. Rev. Phys. Chem. 43 (1992) 693-717: this document generally relates to, inter alia, the presence of ion conductors in solids.

Aniya, Solid State Ionics 136-137 (November 2,2000) 1085-1089: this document generally relates to, inter alia, ion conductor glasses.

Asahara and Izumitani, J. Non-Cryst. Solids 11 (1972) 97-104: this document generally relates to, inter alia, Cu-As-Se glass.

Asokan, et al., Phys. Rev. Lett. 62 (1989) 808-810: this document generally relates to, inter alia, Ge_xSe_{100-x} glasses and their transition from semiconductor-like material to metal-like material.

Baranovskii and Cordes, J. Chem. Phys. 111 (1999) 7546-7557: this document generally relates to, inter alia, ionic glasses and conduction (percolation theory).

Belin et al., Sol. St. Ionics 136-137 (November 2,2000) 1025-1029: this document generally relates to, inter alia, conductivity spectra of the glass $0.5Ag_2S-0.5GeS_2$ and the temperature dependency of the conductivity.

Belin, et al., Solid State Ionics 143 (July 2,2001) 445-455: this document generally relates to, inter alia, the electrical properties of Ag_xGeSe_5I – an argyrodite compound.

Benmore and Salmon, Phys. Rev. Lett. 73 (1994) 264-267: this document generally relates to, inter alia, the characteristics of chalcogenide alloys.

Bernede, Thin Solid Films 70 (1980) L1-L4: this document is in the French language and the Applicant has no translation. It is presently understood to generally relate to, inter alia, metal- Ag_2Se -metal sandwich devices.

Bernede, Thin Solid Films 81 (1981) 155-160: this document generally relates to, inter alia, memories of selenium alloys with metal (e.g., Ag) electrodes, where the "on" memory states require constant voltage.

Bernede, Phys. Stat. Sol. (a) 57 (1980) K101-K104: this document generally relates to, inter alia, metal-Ag₂Se-P systems.

Bernede and Abachi, Thin Solid Films 131 (1985) L61-L64: this document generally relates to, inter alia, metal-insulator-metal thin films with electroforming effects; the films have silver, gold and copper electrodes.

*Bernede, et al., Thin Solid Films 97 (1982) 165-171: this document generally relates to, inter alia, Ag₂Se/Se/Metal thin film sandwiches, which were studied by shape of electrodes (e.g., symmetrical or asymmetrical).

Bernede, et al., Phys. Stat. Sol. (a) 74 (1982) 217-224: this document generally relates to, inter alia, switching in Al-Al₂O₃Ag_{2-x}Se_{1+x} devices.

Bondarev and Pikhitsa, Solid State Ionics 70/71 (1994) 72-76: this document generally relates to, inter alia, Ag⁽⁺⁾/RbAg₄I₅ boundary – depletion layer, and dendritic electrodeposition.

*Boolchand, Asian Journal of Physics (2000) 9, 709-72: this document generally relates to, inter alia, Ge_xSe_{1-x} glasses, which have selenium-rich and germanium-rich clusters, and the intrinsically-broken bond characteristics thereof.

*Boolchand and Bresser, Nature 410 (2001) 1070-1073: published April 26, this document generally relates to, inter alia, Ag₂Se as an electrolyte additive to glass, e.g., GeSe₄. Ge₃₀Se₇₀ glass was found not to work well because of Ag₂Se crystallization.

*Boolchand, et al., J. Optoelectronics and Advanced Materials, 3 (September 2001), 703: this document generally relates to, inter alia, a review of Raman tool scattering of chalcogenide glasses. The floppyness and rigidness is observed. Ge_xSe_{1-x} is disclosed, as is a stoichiometry of $Ge_{25}Se_{75}$.

Boolchand and Grothaus, Eds. Chadi and Harrison, Proc. Int. Conf. Phys, Semicond., 17th (1985) 833-36: this document generally relates to, inter alia, GeSe and GeS glasses and the importance of a broken chemical order therein.

*Boolchand, et al., Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132: this document generally relates to, inter alia, the prediction of glass rigidity in Ge_xSe_{1-x} glass, e.g., $Ge_{23}Se_{77}$.

*Boolchand, et al., Diffusion and Defect Data, Vol. 53-54 (1987) 415-420: this document generally relates to, inter alia, thermal annealing of Ge_xSe_{1-x} films.

*Boolchand, et al., Phys. Rev. B 25 (1982) 2975-2978: this document generally relates to, inter alia, the examination of GeSe glass having Sn impurities by Mossbauer spectroscopy. Investigations into glass network topology, which has an intrinsically broken bond backbone, suggesting Ge and Se rich clusters.

Boolchand, et al., Sol. State Comm. 45 (1983) 183-185: this document generally relates to, inter alia, Ge_xSe_{1-x} and Ge_xS_{1-x} glasses.

*Boolchand and Bresser, Dep. Of ECECS, Univ. Cincinnati 45221-0030: this document generally relates to, inter alia, Ge_xSe_{1-x} and the relation of glass transition temperature to Ge concentration in backbone. Although the publication date of this reference is not known to the Applicant, it was revised October 28, 1999 and is believed to

be publicly available at the University of Cincinnati, Department of Electrical and Computer Engineering and Computer Science.

Bresser, et al., Phys. Rev. Lett. 56 (1986) 2493-2496: this document generally relates to, inter alia, an investigation of c-GeSe₂ structure.

Bresser, et al., J. de Physique 42 (1981) C4-193-C4-196: this document generally relates to, inter alia, the characteristics of GeSe₂ and GeS₂ glasses.

Bresser, et al., Hyperfine Interactions 27 (1986) 389-392: this document generally relates to, inter alia, germanium selenide glasses doped with tellurium.

Cahen, et al., Science 258 (1992) 271-274: this document generally relates to, inter alia, chalcopyrite CuInSe₂ glasses.

Chatterjee, et al., J. Phys. D: Appl. Phys. 27 (1994) 2624-2627: this document generally relates to, inter alia, As_xTe_{100-x-y}Se_y glasses and the current, voltage, and electrical switching behavior. Discloses applicability in read mostly memories.

*Chen and Tai, Appl. Phys. Lett. 37 (1980) 1075-1077: this document generally relates to, inter alia, silver photodoping of Ge_xSe_{1-x} and whisker formation (crystalline Ag₂Se).

Chen and Cheng, J. Am. Ceram. Soc. 82 (1999) 2934-2936: this document generally relates to, inter alia, germanium containing chalcogenides doped with Si₃N₄.

Chen, et al., J. Non-Cryst. Solids 220 (1997) 249-253: this document generally relates to, inter alia, As₁₀Ge₃₀Se₆₀ glasses (and the like) doped with Si₃N₄.

Cohen, et al., J. Non-Cryst. Solids 8-10 (1972) 885-891: this document generally relates to, inter alia, Ge-Te-X glasses as memory devices.

Croitoru, et al., J. Non-Cryst. Solids 8-10 (1972) 781-786: this document generally relates to, inter alia, the physics of conductivity in Ge-containing films.

Dalven and Gill, J. Appl. Phys. 38 (1967) 753-756: this document generally relates to, inter alia, beta-Ag₂Te.

Davis, Search 1 (1970) 152-155: this document generally relates to, inter alia, the subject of amorphous semiconductors as compared to glass.

*Dearnaley, et al., Rep. Prog. Phys. 33 (1970) 1129-1191: this document generally relates to, inter alia, background information about glass and memory.

*Dejus, et al., J. Non-Cryst. Solids 143 (1992) 162-180: this document generally relates to, inter alia, Ag-Ge-Se glass with Ag primarily bonded to Se. The reference discloses glass preparation.

den Boer, Appl. Phys. Lett. 40 (1982) 812-813: this document generally relates to, inter alia, a-Si:H sandwich structures and threshold switching from a low to high conductance.

Drusdau, et al., J. Non-Cryst. Solids 198-200 (1996) 829-832: this document generally relates to, inter alia, work with a-Si:H multilayers optoelectrical properties.

El Bouchairi, et al., Thin Solid Films 110 (1983) 107-113: this document generally relates to, inter alia, Ag_{2-x}Se_{1+x} thin film electrical characteristics and metal-like conduction.

El Gharris, et al., J. Non-Cryst. Solids 155 (1993) 171-179: this document generally relates to, inter alia, photoconductivity of amorphous Se and Ge-Se alloy evaporated films, and reduction of photocurrent by increase of Ge content.

*El Ghrandi, et al., Thin Solid Films 218 (1992) 259-273: this document generally relates to, inter alia, GeSe films deposited by PECVD, Ag evaporation deposition onto glass and photodissolution into same, and optical properties are investigated. GeSe stoichiometries of 30/70 and 25/75, respectively, are disclosed.

*El Ghrandi, et al., Phys. Stat. Sol. (a) 123 (1991) 451-460: this document generally relates to, inter alia, dissolution of Ag into GeSe_{5.5} glass by flash evaporation.

El-kady, Indian J. Phys. 70 A (1996) 507-516: this document generally relates to, inter alia, Ge₂₁Se₁₇Te₆₂ glass and memory, switching, and current controlled negative resistance.

Elliott, J. Non-Cryst. Solids 130 (1991) 85-97: this document generally relates to, inter alia, mechanisms of photodissolution of metals (e.g., Ag) in chalcogenides based on ionic and electronic charge carriers.

*Elliott, J. Non-Cryst. Sol. 130 (1991) 1031-1034: this document generally relates to, inter alia, the photodissolution of metals (e.g., Ag) in chalcogenide glasses and the physics thereof.

Elsamanoudy, et al., Vacuum 46 (1995) 701-707: this document generally relates to, inter alia, studies of quaternary chalcogenide films with Te-As-Ge-Si sandwich structures between electrodes.

*El-Zahed and El-Korashy, Thin Solid Films 376 (November 1, 2000) 236-240: this document generally relates to, inter alia, Ge₂₀Bi_xSe_{80-x} film analysis regarding conduction and changes from p to n type.

Fadel, Vacuum 44 (1993) 851-855: this document generally relates to, inter alia, a study of the switching and memory characteristics of Se₇₅Ge_{25-x}As_x films.

*Fadel and El-Shair, Vacuum 43 (1992) 253-257: this document generally relates to, inter alia, $Se_{75}Ge_7Sb_{18}$ glass electrical conduction and thermal character.

Feng, et al., Phys. Rev. Lett. 78 (1997) 4422-4425: this document generally relates to, inter alia, germanium selenide and germanium sulfide materials.

*Feng, et al., J. Non-Cryst. Solids 222 (1997) 137-143: this document generally relates to, inter alia, the structural character of Ge_xS_{1-x} glass, e.g., hardness and elasticity.

*Fischer-Colbrie, et al., Phys. Rev. B 38 (1988) 12388-12403: this document generally relates to, inter alia, photodiffused $Ag-GeSe_2$ and the interaction between doped Ag with Se atoms and Ge with Ge atoms.

Fleury, et al., Phys. Stat. Sol. (a) 64 (1981) 311-316: this document generally relates to, inter alia, amorphous selenium films and their conductance.

Fritzsche, J. Non-Cryst. Sol. 6 (1971) 49-71: this document generally relates to, inter alia, background information on chalcogenides as semiconductors.

Fritzsche, Annual Review of Mat. Sci. 2 (1972) 697-744: this document generally relates to, inter alia, background information on amorphous semiconductors.

Gates, et al., J. Am. Chem. Soc. (2001): this document generally relates to, inter alia, creating Ag_2Se nanowires by chemical reaction.

Gosain, et al., Jap. J. Appl. Phys. 28 (1989) 1013-1018: this document generally relates to, inter alia, germanium telluride glasses sandwiched in electrodes and the physics thereof.

*Guin et al., J. Non-Cryst. Sol. 298 (March 28,2002) 260-269: this document generally relates to, inter alia, germanium selenide ($GeSe$) glass with low hardness, the

mechanical properties of which are investigated. Stoichiometries of the glass are disclosed as being, inter alia, 10/90, 20/80, and 30/70, respectively.

*Guin et al., J. Am. Ceram. Soc. 85 (June 2002) 1545-1552: this document generally relates to, inter alia, germanium selenide glasses and a study of the hardness properties thereof. Glass stoichometries of 40/60 and 20/80, respectively, are disclosed.

Gupta, J. Non-Cryst. Sol. 3 (1970) 148-154: this document generally relates to, inter alia, switching in chalcogenides.

Haberland and Stiegler, J. Non-Cryst. Solids 8-10 (1972) 408-414: this document generally relates to, inter alia, glasses containing Te, As, Ge, and Si, and pulse sequence and time factors in switching.

Haifz, et al., J. Apply. Phys. 54 (1983) 1950-1954: this document generally relates to, inter alia, As-Se-Cu glasses.

Hajto, et al., Int. J. Electronics 73 (1992) 911-913: this document generally relates to, inter alia, metal/a-Si:H/metal devices.

Hajto, et al., J. Non-Cryst. Solids 266-269 (May 1,2000) 1058-1061: this document generally relates to, inter alia, a-Si:H ion conductors, polarity-dependant digital and analogue memory, and dependency on contact metals.

Hajto, et al., J. Non-Cryst. Solids 198-200 (1996) 825-828: this document generally relates to, inter alia, electroformed V/a-Si:H/Cr devices.

Hajto, et al., Phil. Mag. B 63 (1991) 349-369: this document generally relates to, inter alia, p+ type amorphous Si memory structures with polarity dependent analogue switching.

Hayashi, et al., Japan. J. Appl. Phys. 13 (1974) 1163-1164: this document generally relates to, inter alia, Au-CdS(CdSe)-Au systems and metal-Se-Sn-SnO₂ systems.

*Hegab, et al., Vacuum 45 (1994) 459-462: this document generally relates to, inter alia, Ge₂₀M₇₅Sb₁₈ glass electrical conduction and thermal character.

Hirose and Hirose, J. Appl. Phys. 47 (1976) 2767-2772: this document generally relates to, inter alia, Ag photodoped As₂S₃, polarized switching, and dendrite formation.

Hong and Speyer, J. Non-Cryst. Solids 116 (1990) 191-200: this document generally relates to, inter alia, Cd-Ge-As glass with Ag contacts.

Hosokawa, J. Optoelectronics and Advanced Materials 3 (2001) 199-214: this document generally relates to, inter alia, x-ray scattering experiments on glassy Ge_xSe_{1-x}.

Hu, et al., J. Non-Cryst. Solids 227-230 (1998) 1187-1191: this document generally relates to, inter alia, a-Si:H with Cr and V electrodes.

Hu, et al., Phil. Mag. B. 74 (1996) 37-50: this document generally relates to, inter alia, a-Si:H glasses doped with Cr and analogue memory.

Hu, et al., Phil. Mag. B 80 (January 1, 2000) 29-43: this document generally relates to, inter alia, a-Si:H films doped with Cr-p+.

Iizima, et al., Solid State Comm. 8 (1970) 153-155: this document generally relates to, inter alia, switching and memory effects in As-Te-I^{1,2} and As-Te-Ge-Si³ glass systems. Thermal breakdown is proposed switching effect.

Ishikawa and Kikuchi, J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066: this document generally relates to, inter alia, Ge₂S₂ films with Ag photodissolved therein.

*Iyetomi, et al., J. Non-Cryst. Solids 262 (February 2000) 135-142: this document generally relates to, inter alia, Ag/Ge/Se glasses as a composite of GeSe₂ and Ag₂Se (a fast ion conductor) and polarizability of Se ions.

Jones and Collins, Thin Solid Films 40 (1977) L15-L18: this document generally relates to, inter alia, switching in Se films and switching back with reverse pulse.

Joullie and Marucchi, Phys. Stat. Sol. (a) 13 (1972) K105-K109: this document generally relates to, inter alia, As₂Se₇ glass.

Joullie and Marucchi, Mat. Res. Bull. 8 (1973) 433-442: this document generally relates to, inter alia, As₂Se₅ film conduction and switching.

Kaplan and Adler, J. Non-Cryst. Solids 8-10 (1972) 538-543: this document generally relates to, inter alia, thermal effects on semiconductor switching.

*Kawaguchi, et al., J. Appl. Phys. 79 (1996) 9096-9104: this document generally relates to, inter alia, Ag-rich chalcogenide glass, Ge₃S₇-Ag and Ge₃₀Se₇₀-Ag, max Ag content of 67%, graphs phase diagram, and discloses that Ag works better than Cu.

*Kawaguchi and Masui, Jpn. J. Appl. Phys. 26 (1987) 15-21: this document generally relates to, inter alia, silver photodoping of chalcogenide films, e.g., Ge₃₀Se₇₀ films.

*Kawasaki, et al., Solid State Ionics 123 (1999) 259-269: this document generally relates to, inter alia, the electrical properties of Ag_x(GeSe₃)_{1-x}, conductivity EMF measurements, glass composition, X-ray diffraction, T_g and T_c, Ag ion transport, and glass structure.

*Kluge, et al., J. Non-Cryst. Solids 124 (1990) 186-193: this document generally relates to, inter alia, photodiffusion of silver into Ge_xSe_{100-x} layers, how this differs from ion beam induced diffusion, Ge₃₀Se₇₀ stoichiometry, Ag₂Se, and percolation threshold.

*Kolobov, J. Non-Cryst. Solids 198-200 (1996) 728-731: this document generally relates to, inter alia, p-type conductive chalcogenides, materials, and physics thereof.

*Kolobov, J. Non-Cryst. Solids 137-138 (1991) 1027-1030: this document generally relates to, inter alia, doped and undoped glass layers as a p-n junction.

Korkinova and Andreichin, J. Non-Cryst. Solids 194 (1996) 256-259: this document generally relates to, inter alia, polarization of chalcogenide glass as depending on the materials used for electrode contacts.

*Kotkata, et al., Thin Solid Films 240 (1994) 143-146: this document generally relates to, inter alia, GeSe glass switching and film thickness, memory, current filament, chemical and mechanical switching properties, and discloses that heat treatment or aging improves switching.

Lakshminarayan, et al., J. Instn. Electronics & Telecom. Engrs. 27 (1981) 16-19: this document generally relates to, inter alia, tellurium-containing chalcogenide glasses.

Lal and Goyal, Indian Journal of Pure & Appl. Phys. 29 (1991) 303-304: this document generally relates to, inter alia, theory on chalcogenide switching.

*Leimer et al., Phys. Stat. Sol. (a) 29 (1975) K129-K132: this document generally relates to, inter alia, germanium selenide glass polarization behavior, e.g., inductive and capacitive components.

*Leung, et al., Appl. Phys. Lett. 46 (1985) 543-545: this document generally relates to, inter alia, photoinduced diffusion of Ag into Ge_xSe_{1-x} and techniques for same.

Matsushita, et al., Jap. J. Appl. Phys. 11 (1972) 1657-1662: this document generally relates to, inter alia, $Se-SnO_2$ film switching and reversibility.

Matsushita, et al., Jpn. J. Appl. Phys. 11 (1972) 606: this document generally relates to, inter alia, polarized memory effect in Se films.

Mazurier, et al., Journal de Physique IV 2 (1992) C2-185 - C2-188: this document generally relates to, inter alia, Te-based glasses.

Messoussi, et al., Mat. Chem. And Phys. 28 (1991) 253-258: this document generally relates to, inter alia, selenium films and Bi electrodes.

*Mitkova and Boolchand, J. Non-Cryst. Solids 240 (1998) 1-21: this document generally relates to, inter alia, the analysis of Group IV and V chalcogenides.

*Mitkova and Kozicki, J. Non-Cryst. Solids 299-302 (May 14, 2002) 1023-1027: this document generally relates to, inter alia, photodissolution of Ag into Se-rich Ge-Se glasses for use in memory devices. The information disclosed in this reference was available to and known by the inventors prior to the filing of the application.

*Mitkova, et al., Phys. Rev. Lett. 83 (1999) 3848-3851: this document generally relates to, inter alia, Ag doped chalcogenides, $Ge_{20}Se_{80}$ stoichiometry is disclosed, Se rich glasses, Ge rich glasses, stoichiometric glasses, and presence of Ag_2Se .

*Miyatani, J. Phys. Soc. Japan 34 (1973) 423-432: this document generally relates to, inter alia, electrical and ionic properties of solid solutions (e.g., doped glass), polarization, conductivity, Ag_2Se and Cu_2Se .

Miyatani, J. Phys. Soc. Japan 13 (1958) 317: this document generally relates to, inter alia, experiments regarding the electronic conductivity, ionic conductivity, hall constant, thermoelectric power, and Nernst coefficient of Ag_2Se as function of the e.m.f., E, the galvanic cell, or the deviation from stoichiometric composition.

*Miyatani, J. Phys. Soc. Japan 14 (1959) 996-1002: this document generally relates to, inter alia, Ag_2Te and Ag_2Se ion conduction and the chemical potential of silver ions.

Mott, J. Non-Cryst. Sol. 1 (1968) 1-17: this document generally relates to, inter alia, glasses with vanadium or iron.

*Nakayama, et al., Jpn. J. Appl. Phys. 32 (1993) 564-569: this document generally relates to, inter alia, electrically erasable nonvolatile memories in chalcogenide films of $\text{As}_x\text{Sb}_y\text{Te}_z$, flash evaporative deposition techniques, a high set-voltage compared to read-voltage, V_t creates a “filament,” and refresh-type pulse.

*Nakayama, et al., Jpn. J. Appl. Phys. 39 (November 15, 2000) 6157-6161: this document generally relates to, inter alia, phase transition random access memory (PRAM) made of chalcogenide glass.

*Nang et al., Jap. J. App. Phys. 15 (1976) 849-853: this document generally relates to, inter alia, $\text{Ge}_x\text{Se}_{1-x}$ electrical and optical properties; it also discloses $\text{Ge}_{.80}\text{Se}_{.20}$, $\text{Ge}_{.60}\text{Se}_{.40}$, and $\text{Ge}_{.50}\text{Se}_{.50}$.

Narayanan, et al., Phys. Rev. B 54 (1996) 4413-4415: this document generally relates to, inter alia, chalcogenide glass switching as thermally originated.

*Neale and Aseltine, , IEEE Transactions On Electron Dev. Ed-20 (1973) 195-209: this document generally relates to, inter alia, read mostly memories with chalcogenides (e.g., Ge, Te), also discloses “floating gate,” and material combinations including Ge and Se.

Ovshinsky and Fritzsche, Metallurgical Transactions 2 (1971) 641-645: this document generally relates to, inter alia, reversible changes in amorphous Si, Be, and B using a laser to write and erase.

Ovshinsky, Phys. Rev. Lett. 21 (1968) 1450-1453: this document generally relates to, inter alia, rapid and reversible resistive switching by electric field in amorphous semiconductors.

Owen, et al., IEE Proc. 129 (1982) 51-54: this document generally relates to, inter alia, a-Si:H, gold or aluminum dots and silver paste.

Owen, et al., Phil. Mag. B 52 (1985) 347-362: this document generally relates to, inter alia, photoinduced chalcogenide effects (As_2S_3) both reversible and irreversible.

*Owen, et al., Int. J. Electronics 73 (1992) 897-906: this document generally relates to, inter alia, threshold and memory switching a-Si:H ion conductor, polarity-dependant digital memory, analogue memory, and device operation dependency on metal contacts.

Pearson and Miller, App. Phys. Lett. 14 (1969) 280-282: this document generally relates to, inter alia, glass diodes.

*Pinto and Ramanathan, Appl. Phys. Lett. 19 (1971) 221-223: this document generally relates to, inter alia, electric field inducement of glass switching "filamentary" path.

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*Thornburg, J. Elect. Mat. 2 (1973) 3-15: this document generally relates to, inter alia, division of chalcogenides into stoichiometric compounds with no changes upon crystallization, stoichiometric compounds with changes upon crystallization, and non-stoichiometric which phase separate on crystallization, As₂Se₃ and filament growth as a function of bias applied.

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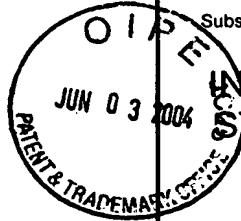
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				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	Not Known
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U.S. PATENT DOCUMENTS

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
	BA	WO 02/21542	03/14/2002	Kozicki et al.		
	BB	WO 00/48196	08/17/2000	Kozicki et al.		
	BC	WO 97/48032	12/18/1997	Kozicki et al.		
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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3

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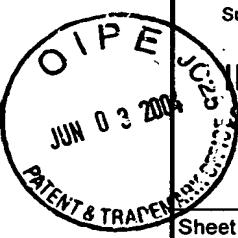
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/076,486
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				First Named Inventor	Stephen L. Casper
				Group Art Unit	2818
				Examiner Name	Not Known
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CA2		Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
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CD2		El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.	
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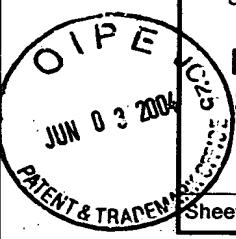
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5 of 8

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	CJ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As ₂ Se ₇ before switching, <i>Phys. Stat. Sol. (a)</i> 13 (1972) K105-K109.
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Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

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Attorney Docket Number	M4065.0479/P479

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/076,486
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Sheet	8	of	8	First Named Inventor	Stephen L. Casper
				Group Art Unit	2818
				Examiner Name	Not Known
				Attorney Docket Number	M4065.0479/P479

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	CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in $GexSe_{1-x}$ and As_xSe_{1-x} systems, <i>J. Non-Cryst. Solids</i> 261 (2000) 277-281.	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Inventors: Stephen L. Casper et al.

Atty Docket No.: M4065.0479/P479

Application No.: 10/076,486

Title: PROGRAMMABLE CONDUCTOR RANDOM ACCESS MEMORY AND METHOD FOR
SENSING SAME

Filing Date: February 19, 2002

Documents Filed:

Amendment w/copies 1449 and two date-stamped postcards
Third IDS w/Appendix A, PTO/SB/08A and 79 references
Form PTO-2038
Amendment Transmittal

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Date: September 16, 2002

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No.: M4065.0479/P479
(PATENT)

In re Patent Application of:
Stephen L. Casper et al.

Application No.: 10/076,486

Group Art Unit: 2818

Filed: February 19, 2002

Examiner: M. Tran

For: PROGRAMMABLE CONDUCTOR
RANDOM ACCESS MEMORY AND
METHOD FOR SENSING SAME

THIRD INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO/SB/08. It is respectfully requested that the subject matter of the documents be expressly considered during the prosecution of this application and that the documents be made of record therein and appear among the "References Cited" on any patent to issue from this application. A copy of each document is attached.

This Third Information Disclosure Statement is being filed concurrently with an Amendment.

A brief explanation of relevance of certain non-patent documents listed on Form PTO/SB/08 is provided and attached hereto as Appendix A. The brief explanation provided for each document is not tantamount to an admission that a document is "material" or that it qualifies as prior art. The Examiner is respectfully requested to utilize

Appendix A only as a tool by which to better categorize the documents for substantive use in examining the claims of the application.

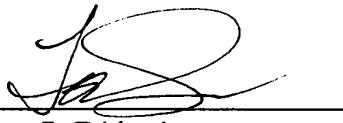
Documents discussed in Appendix A marked with an asterisk (*) are indicated to be potentially more relevant than others. Such marking is provided only to assist the Examiner; however, the Examiner is requested to thoroughly review all documents cited herein.

In accordance with 37 C.F.R. § 1.97(g), the filing of this Third Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 C.F.R. § 1.56(a) exists. It is submitted that this Third Information Disclosure Statement is in compliance with 37 C.F.R. § 1.98 and the Examiner is respectfully requested to consider and cite the listed documents.

The Director is hereby authorized to charge the \$180.00 fee as required by 37 C.F.R. §1.17(p) to the undersigned attorneys' credit card. Form PTO-2038 is attached. The Commissioner also is authorized to charge any deficiency in the fees filed, asserted to be filed, or which should have been filed herewith (or with any paper hereafter filed in this application by this firm), to our Deposit Account No. 04-1073, under Order No. M4065.0479/P479.

Dated: September 16, 2003

Respectfully submitted,

By 
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Attorneys for Applicants

APPENDIX A

Japanese patent application publication No. 56126916A by Akira: this published application generally relates to, inter alia, diffusing selenium with high accuracy into a chalcogenide with silver by use of photoresist and thermal treatment.

*Axon Technologies Corp., *Technology Description: Programmable Metallization Cell*: this believed publication generally relates to, inter alia, use of chalcogenides doped with metal such as silver or copper to create solid state switch with lower voltage requirement.

Helbert et al., SPIE Vol. 333 Submicron Lithography (1982): this publication generally relates to, inter alia, hybrid ultragraphic process using both electron beam and conventional optical exposure within the same device level with a photoresist.

Hilt, dissertation (1999): this publication generally relates to, inter alia, stability of chalcogenides such as Ge_xSe_{1-x} with Ag doping by photodissolution and thermal diffusion.

Hirose et al., Phys. Stat. Sol. (1980): this publication generally relates to, inter alia, switch and memory phenomena in amorphous As_2S_3 with photo-doped Ag, including new mechanism, electrical reliability, rapid memory performance, thermal characteristics and durability

Holmquist et al., 62 J. Amer. Ceram. Soc., No. 3-4 (March-April 1979): this publication generally relates to, inter alia, reactions and diffusion of Ag in arsenic chalcogenide glass below the glass transition temperature, including solubility information and concentration dependence of Ag diffusion in these glasses.

Hugggett et al., 42 Appl. Phys. Lett., No. 7 (April 1983): this publication generally relates to, inter alia, reactive sputter etching to develop silver-sensitized Ge_xSe_{1-x} photoresist.

Kawaguchi et al., 164-166 J. Non-Cryst. Solids (1993): this publication generally relates to, inter alia, deposition mechanism of Ag particles on Ag-rich Ag-As-S glass from a view-point of electrical effects.

*Kolobov and Elliott, Advances in Physics (1991): this publication generally relates to, inter alia, photodoping (photodiffusion/photodissolution) of amorphous chalcogenides by metals, particularly silver.

*Kozicki et al., Superlattices and Microstructures, 27 (2000): this publication generally relates to, inter alia, solid solutions of metals (e.g., silver) in arsenic trisulfide and their physical and electrical characteristics.

*Kozicki et al., Microelectronic Engineering, vol. 63/1-3 (2002): this publication generally relates to, inter alia, the photodiffusion of Ag into germanium selenide glass films, the amount of Ag that can be incorporated in to such a film by photodiffusion, and the characteristics of the resulting doped films.

*Kozicki et al., Proceedings of the 1999 Symposium on Solid State Ionic Devices (1999): this publication generally relates to, inter alia, physical and electrical characteristics of metal doped chalcogenide films (photodoped $\text{Ag}_4\text{As}_2\text{S}_3$) between electrodes, useful in memories, configurable connections, and self-repairing interconnections.

*Kozicki and Mitkova, Proceedings of the XIX International Congress on Glass, Society for Glass Technology (2001): this publication generally relates to, inter alia, the physical effects of introduction of Ag into chalcogenide glasses, where introduction is by photodiffusion.

McHardy et al., 20 J. Phys. C.: Solid State Phys. (1987): this publication generally relates to, inter alia, sensitivity and high resolution of metals in amorphous chalcogenides by electron and UV radiation.

Owen et al., Nanostructure Physics and Fabrication (1989): this publication generally relates to, inter alia, photo-induced structural or physico-chemical changes of amorphous chalcogenides when exposed to light/irradiation, affecting chemical solubility.

Shimizu et al., 46 B. Chem Soc. Japan, No. 12 (1973): this publication generally relates to, inter alia, electric conductivity increase by increasing Ag-photodoping of chalcogenide glass.

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				Examiner Name	M. Tran
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U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)	MM-DD-YYYY		
AA	6,469,364		10/2002	Kozicki	
AB	2002/0168820 App.		11/2002	Kozicki	
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AV	5,360,981		11/1994	Owen et al.	
AW	5,512,328		4/1996	Yoshimura et al.	
AX	5,512,773		4/1996	Wolf et al.	
AY	5,726,083		3/1998	Takaishi	
AA1	5,841,150		11/1998	Gonzalez et al.	
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2

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4

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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Art Unit	2818
Examiner Name	M. Tran

Attorney Docket Number M4065.0479/P479

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				Application Number	10/076,486
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				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	3	of	4	Attorney Docket Number	M4065.0479/P479

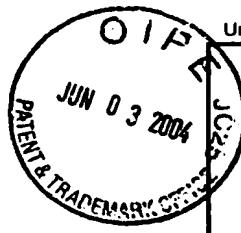
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BB						

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				Application Number	10/076,486
				Filing Date	February 19, 2002
				First Named Inventor	Stephen L. Casper et al.
				Group Art Unit	2818
				Examiner Name	M. Tran
Sheet	4	of	4	Attorney Docket Number	M4065.0479/P479

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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